# Effect of atmosphere on superplastic deformation behavior in nanocrystalline liquid-phase-sintered silicon carbide with Al<sub>2</sub>O<sub>3</sub>-Y<sub>2</sub>O<sub>3</sub> additions

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Nanocrystalline  $\beta$ -SiC with additions of 5.135 wt% Al<sub>2</sub>O<sub>3</sub> and 3.867 wt% Y<sub>2</sub>O<sub>3</sub> was subjected to tensile deformation in order to study its microstructural behavior under the dynamic process. The liquid-phase-sintered body had a relative density of >95% and an average grain size of 190 nm. Tension tests were conducted at initial strain rates range from  $3 \times 10^{-4}$  to  $2 \times 10^{-5}$  s<sup>-1</sup>, in the temperature range 1873–2048 K, in both argon and N<sub>2</sub> atmospheres. Although grain-boundary liquids formed by the additions vaporized concurrently with the decomposition of SiC and grain growth, the maximum tensile elongation of 60% was achieved in argon. The grain-boundary amorphous phase formed a crystalline phase during testing in an N<sub>2</sub> atmosphere and fracture occurred at <8% elongation. Grain-boundary sliding was still the dominant mechanism for deformation. © 2002 Kluwer Academic Publishers

#### 1. Introduction

Silicon carbide (SiC) is difficult to densify without sintering additives because of the covalent nature of the Si-C bonding and the low self-diffusion coefficient. SiC has attracted much attention as a structural material since Prochazka [1] reported on it in 1973. With boron and carbon as additives, Prochazka used pressureless sintering to fabricate dense SiC that maintained excellent strength up to 1773 K. The additives lowered the grain-boundary energy and promoted sintering. Superior mechanical strength at high temperature was achieved because the additives were incorporated into the SiC as a solid solution.

In liquid-phase sintering, Suzuki [2] fabricated a sintered body with a density of >97% of the theoretical value using  $\beta$ -SiC powder with Al<sub>2</sub>O<sub>3</sub> as an additive. Omori and Takei [3] fabricated  $\beta$ -SiC with 96.8% of full density using Al<sub>2</sub>O<sub>3</sub> and Y<sub>2</sub>O<sub>3</sub> additives. The sintering temperatures of these liquid-phase-sintered materials were >2173 K, as high as those in Prochazka's solid-phase sintering, and phase transformation from isotropice  $\beta$  grains to anisotropic  $\alpha$  grains occurred during sintering.

Superplasticity is phenomenologically defined as the ability of a polycrystalline material to exhibit an extraordinary large elongation during tension testing. Ceramic superplasticity is generally exhibited in polycrystals with an average grain size of  $<1 \ \mu$ m.

Recently, dense nanocrystalline SiC with oxide additives was fabricated by hot pressing [4]. In liquid-phasesintered  $\beta$ -SiC, an amorphous phase was observed at grain boundaries [5–7]. Liquid-phase-sintered SiC with an amorphous phase at the grain boundaries can be deformed at lower deformation temperatures, lower flow stresses, and higher strain rates in comparison with boron and carbon-doped SiC with no amorphous phase at the grain boundaries.

The superplastic deformation temperature of liquidphase sintered  $\beta$ -SiC in argon (>1973 K) [5–9], however, was higher that of Si<sub>3</sub>N<sub>4</sub> in N<sub>2</sub> (1873 K) [10]. Therefore, the vaporization of amorphous phase and grain growth during deformation prevented large elongation.

The authors of this study also investigated the effect of atmosphere on the weight loss of liquid-phase sintered  $\beta$ -SiC with oxide additives during the heat treatment, and found that the weight loss in N<sub>2</sub> was suppressed about 1/2 to 1/3 in comparison with the weight loss in Ar [11]. Jun and co-workers [12] compared the sintering behavior of SiC in both argon and N<sub>2</sub> atmospheres and reported that grain growth and phase transformation from  $\beta$  to  $\alpha$  were suppressed in N<sub>2</sub>. Accordingly, deformation of SiC with an amorphous phase at high temperature is influenced by dynamic microstructural change and atmosphere during those tests.

For this study, the effect of atmosphere on deformation behavior and dynamic microstructural change of liquid-phase-sintered  $\beta$ -SiC with Al<sub>2</sub>O<sub>3</sub> and Y<sub>2</sub>O<sub>3</sub> was investigated in both argon and N<sub>2</sub> atmospheres.

## 2. Experimental procedure

The starting material was ultrafine  $\beta$ -SiC powder (T-1 grade, Sumitomo-Osaka Cement Co., Tokyo, Japan) fabricated by plasma-enhanced chemical vapor deposition. The average grain size was 90 nm. The raw powder included 3.27 wt% free carbon. Excess free carbon prevents densification during sintering, therefore, after the raw powders had been annealed in air at 873 K for 2 h, they were soaked in hot HF and HNO<sub>3</sub> solution for 1 h and then rinsed in deionized water, which reduced the carbon content to 1.27 wt%. The powder was mixed with 5.135 wt% Al<sub>2</sub>O<sub>3</sub> (AKP-20 grade, Sumitomo Chemical Co., Tokyo, Japan), 3.867 wt% Y<sub>2</sub>O<sub>3</sub> (99.9% pure, Shinetsu Chemical Co., Tokyo, Japan) in *n*-hexane, using a SiC ball mill. Sintering was performed by hot-pressing under 30 MPa pressure, at 2048 K, for 30 min in argon. The relative bulk density was more than 95%. The as-sintered body was cut with a diamond cutter and ground using a diamond wheel. Tensile samples were dog-bone shaped, with a rectangular cross section  $(1 \text{ mm} \times 0.8 \text{ mm})$  and a gauge length of 4.4 mm. The sample surfaces were mirror-polished with 6  $\mu$ m diamond paste.

Tension tests were conducted using a universal testing machine with furnace at constant crosshead speeds, at initial strain rates from  $3 \times 10^{-4}$  to  $2 \times 10^{-5}$  s<sup>-1</sup>, in the temperature range 1873–2048 K, in both argon and N<sub>2</sub> atmospheres. The specimen was gripped by chucking devices, which were made of sintered SiC with the additions of boron and carbon. The degree of sample deformation was measured from the displacement of the crosshead. The tensile direction was perpendicular to the hot-pressing direction.

The true strain,  $\varepsilon_t$ , is defined as

$$\varepsilon_{\rm t} = \ln(l/l_0) \tag{1}$$

where l and  $l_0$  are the deformed and the original gauge length, respectively.

Assuming homogeneous deformation, true stress,  $\sigma_t$ , can be calculated by the relationship,

$$\sigma_{\rm t} = \frac{P}{A_0} \exp(\varepsilon_{\rm t}) \tag{2}$$

where P is the applied load and  $A_0$  the cross section of the original sample.

The samples were observed after deformation, using scanning electron microscopy on the polished and plasma-etched surface, with  $CF_4 + O_2$  (8%) gas. The average grain size for the linear intercept length is defined as follow [13].

$$d_{\rm av} = 1.776L$$
 (3)

Here,  $d_{av}$  is the average grain size and L the linear intercept length.

X-ray analysis was also conducted, to detect phase transformation and crystallization of the grainboundary phase. The polytype contents of SiC were calculated using the method described by Tanaka [14].

The as-sintered material was prepared by polishing and argon-ion-beam thinning for observation by transmission electron microscope (TEM). High-resolution TEM (HRTEM) observation was performed using a 200 kV TEM (EM002B, TOPCON, Tokyo, Japan) with a point-to-point resolution of 0.18 nm. The grainboundary composition was analyzed by both electron energy loss spectroscopy (EELS) and energy dispersive X-ray spectroscopy (EDX) using a scanning transmission electron microscope (Model No. HB601UX, VG Microscopes, East Grinstead, UK) with a minimum probe size of 0.22 nm.

Thermogravimetry-differential thermal analysis (TG-DTA: STA409, NETZSCH, Waldkraiburg, Germany) was performed in argon atmosphere to study the behavior of grain-boundary phase during tension testing. The heating rate was 20 K/min.

## 3. Results

## 3.1. Mechanical behavior

The true stress-true strain curves at the initial strain rate of  $5 \times 10^{-5}$  s<sup>-1</sup> in argon are shown in Fig. 1. Flow stress decreased with increasing temperature. The maximum tensile elongation of 60% was obtained at 1998 K.

The true stress-true strain curves at the initial strain rate of  $5 \times 10^{-5}$  s<sup>-1</sup> in N<sub>2</sub> are shown in Fig. 2. Strain softening was observed in all experimental conditions. All specimens were fractured at <8% elongation in spite of maximum true stress about <10 MPa.

## 3.2. Microstructural observation

Microstructural change before and after the tension tests is shown in Fig. 3. The as-sintered body was composed of equiaxed, fine grains (Fig. 3a). The grains were fully wetted. In deformed specimen in argon, grain growth occurred, but no anisotropy was observed. The grain size at fracture (50% elongation) was 490 nm. The vaporization of the grain-boundary phase is visible in



*Figure 1* True stress-true strain curves at 5E-5 s<sup>-1</sup> in Ar.



Figure 2 True stress-true strain curves at 5E-5  $s^{-1}$  in  $N_2.$ 

Fig. 3b. The submicron size of the cavities was also observed. On the other hand, in deformed specimen in  $N_2$ , the vaporization of grain-boundary phase was suppressed in comparison with that in argon (Fig. 3c). The grain size at fracture (7.3% elongation) was 360 nm. The cracks were propagated from sample surface into the inside of sample in the vertical direction of tensile axis (Fig. 3d).

An HRTEM image of the grain boundary in an assintered sample is shown in Fig. 4. An amorphous layer about 1 nm thick was evident at the grain boundary.

The energy-loss near-edge structure (ELNES) results for both grain and grain boundary before tension tests are shown in Fig. 5. The grain-boundary spectrum reveals that the amorphous layer contained aluminum, yttrium, and oxygen segregation those were not detected



Figure 4 High-resolution TEM image at grain boundary in as-sintered material.



*Figure 3* Microstructure of (a) as-sintered SiC, (b) after tensile deformation in Ar (2023 K, 2E-4 s<sup>-1</sup>, 50% elongation, tensile axis is horizontal), (c) after tensile deformation in N<sub>2</sub> (×50 K, 2023 K, 5E-5 s<sup>-1</sup>, 7.3% elongation, tensile axis is horizontal) and (d) after tensile deformation in N<sub>2</sub> (×100, 2023 K, 5E-5 s<sup>-1</sup>, 7.3% elongation, tensile axis is horizontal).



*Figure 5* ELNES results for Al-L edges, Si-L edges, Y-M edge, C-K edge, and O-K edge at grain and grain boundary in as-sintered material.



*Figure 6* High-resolution TEM image at grain boundaries after (a) tensile deformation in Ar (1998 K, 5E-5 s<sup>-1</sup>, 60% elongation) and (b) tensile deformation in N<sub>2</sub> (1998 K, 5E-5 s<sup>-1</sup>, 5.0% elongation).

in the SiC spectrum. The grain-boundary spectrum also reveals that the amorphous layer contained silicon and carbon segregation that was detected in the SiC spectrum. Although signals from Si and C probably originated from the bulk grain, silicon carbide, a Si-Al-Y-O glass is expected at the grain boundaries judging from the ELNES results.

HRTEM images of the grain boundary in deformed samples in both argon and  $N_2$  are shown in Fig. 6. In samples deformed in argon, the amorphous phase was difficult to observe in most of grain boundaries



*Figure 7* ELNES results for Al-L edges, Si-L edges, Y-M edge, C-K edge, and O-K edge at grain boundary after tensile deformation in Ar (1998 K,  $5E-5 s^{-1}$ , 60% elongation).



Figure 8 TG-DTA curves of as-sintered SiC in Ar.

as shown in Fig. 6a. In samples deformed in  $N_2$ , a crystalline phase was observed at many triple points and multi grain junctions. EDX results showed that this crystalline phase contained aluminum and nitrogen.

ELNES results for grain boundaries before and after tension tests in argon are shown in Fig. 7. The peaks for aluminum and oxygen have completely disappeared and that of yttrium has almost disappeared after tensile deformation in argon.

# 3.3. TG-DTA analysis

TG-DTA curves in argon are shown in Fig. 8. The increasing of weight loss at the temperature range from room temperature to 1300 K was originated from residual gas in the furnace. Weight loss began about 1300 K and showed about 6% at 2000 K. The endothermic reaction suddenly increased at about 2000 K.

#### 3.4. XRD analysis

The crystalline phase of the as-sintered material was a  $\beta$ -SiC(3C) single phase. No phase transformation from  $\beta$  to  $\alpha$  was detected after deformation in either argon or N<sub>2</sub> atmospheres. Amounts of the crystalline phase at triple points and multi grain junctions in the sample deformed in N<sub>2</sub> were below the detection limit.

#### 4. Discussion

In deformed samples, no phase transformation or multiplication of dislocation were found. The SiC grains retained their equiaxed shape, when grain growth occurred during large deformation. Therefore,

TABLE I Results of tension tests

Atmosphere	Temperature (K)	Strain rate $(s^{-1})$	Elongation (%)	Weight loss (%)
Ar	1973	$5 \times 10^{-5}$	39	11.8
	1998	$5 \times 10^{-5}$	60	11.2
	2048	$5 \times 10^{-5}$	44	12.0
N <sub>2</sub>	1998	$5 \times 10^{-5}$	5.0	4.7
	2023	$5 \times 10^{-5}$	7.3	4.8

grain-boundary sliding is identified as the major mechanism of deformation in this material. The amorphous films at the grain boundaries became liquid at temperatures higher than the glass-transition temperature and also could be a supercooled liquid below that temperature. Such films were beneficial to deformation at high temperature. Authors of this work reported that SiC with the addition of Al showed rapid strain hardening by the vaporization of grain-boundary phase during tension test [15].

#### 4.1. Ar atmosphere

The plateau region which specimen deformed at constant stress was obtained in Fig. 1. In this region, the deformation is thought to be enhanced by the amorphous phase. The weight loss during tension tests (11-12 wt%) was higher than the weight of sintering additive as shown in Table I. Therefore, the decomposition of SiC was thought to be occurring concurrently with the vaporization of the grain-boundary phase.

An oxide layer is formed on the surface of the raw SiC powder, in addition to the oxides used as sintering additives. This adsorbed oxygen remains within the sintered body and reacts with SiC at temperatures greater than 1573 K and decomposes the SiC as follows [16].

$$SiC(s) + 2SiO_2(1) \rightarrow 3SiO(g) \uparrow + CO(g) \uparrow (4)$$

In the Al<sub>2</sub>O<sub>3</sub>-Y<sub>2</sub>O<sub>3</sub> system, the decomposition of SiC and the vaporization of additives occur at the same time at >1973 K [16].

$$\begin{split} \text{SiC}(s) + \text{Al}_2\text{O}_3(s) &\to \text{Al}_2\text{O}(g) \uparrow + \text{SiO}(g) \uparrow + \text{CO}(g) \uparrow \\ (5) \\ \text{SiC}(s) + \text{Y}_2\text{O}_3(s) &\to \text{Y}_2\text{O}(g) \uparrow + \text{SiO}(g) \uparrow + \text{CO}(g) \uparrow \\ (6) \end{split}$$

Grande and co-workers investigated the evaporation of liquid-phase sintered SiC during sintering by thermogravimetry in a graphite furnace. They reported that the amount of yttrium-containing secondary phase did not significantly reduce during heat treatment at 2093 K for 6 h. However, in our experiment at the temperature range from 1973 K to 2023 K, amorphous phase was partially remained at the grain boundaries. Therefore, the occurrence of cavitation at triple points during superplastic deformation may enhance the vaporization of grain-boundary phase.

It is obvious that the presence of oxygen is one of the origins for the decomposition of SiC and the vaporization of sintering additives. Therefore, the weight-loss can be affected by the total amount of oxygen content, basically the amount of the oxygen impurity, that of the oxide additives and oxygen partial pressure (Po<sub>2</sub>).

In this atmosphere, the deformation temperature should be lower than 1973 K to suppress the vaporization of grain-boundary phase and the decomposition of SiC. The samples, however, exhibited only 16% elongation at the initial strain rate of  $2 \times 10^{-5}$  s<sup>-1</sup> at 1873 K.

#### 4.2. N<sub>2</sub> atmosphere

Dissolved nitrogen inhibits the atomic transport processes responsible for sintering of SiC [12, 17]. For thermal decomposition and vaporization as in the present case, however, reaction at the interfaces between SiC grains and secondary phases would be a dominant mechanism rather than the diffusion or mass transport of chemical species. Originally, the crystallization of grain-boundary phase was considered to be preventing weight-loss. The heat treatment in N2 suppressed the vaporization and decomposition of grain-boundary phase, and promoted nitrogen substitution within grainboundary phase. Nitrogen can dissolve in silica or aluminosilicate glasses physically or chemically [18]. Although physical solubility in aluminosilicates is considered to be small [19], it may cause of the increase in weight as well as the dissolution of nitrogen into SiC. In the case of chemical dissolution, on the other hand, nitrogen dissolution proceeds by the substitution of oxygen ions into nitrogen in the network structure. According to Hwang et al. [19] chemical dissolution of nitrogen in oxynitride melts takes place as following reaction when the oxidation reaction of SiC is involved:

$$N_2 + SiC + (O) \rightarrow 2(N) + (Si) + CO \uparrow (7)$$

where the parentheses in the equation indicate solution in the melts. The reaction indicates the conversion of  $(SiO_2)$  in the Al-Si-O glass to  $(Si_3N_4)$  according to the reaction.

$$2N_2 + 2SiC + (SiO_2) \rightarrow (Si_3N_4) + 2CO \uparrow (8)$$

Similarly, formation reaction of AlN can be written as

$$2N_2 + 3SiC + (2Al_2O_3) \rightarrow (4AlN) + 3SiO \uparrow + 3CO \uparrow$$
(9)

or

$$3N_2 + 3SiC + (Al_2O_3) \rightarrow (2AlN) + (Si_3N_4) + 3CO \uparrow$$
(10)

Elongation in N<sub>2</sub> atmosphere was always <8% at the different strain rates. Such brittle fracture was a result of the inhibition of grain-boundary sliding by crystallization of the grain-boundary phase. However, as we reported previously [11], and N<sub>2</sub> atmosphere has the advantage over an argon atmosphere for suppressing vaporization of the grain-boundary phase and the decomposition of SiC. Weight loss during testing in N<sub>2</sub> was about 5% as shown in Table I. Therefore, the amorphous phase, which is stable in an N<sub>2</sub> atmosphere, is very important for achieving even larger deformation in liquid-phase-sintered SiC.

# 5. Conclusions

Tension tests were conducted on liquid-phase-sintered SiC with additions of 5.135 wt% Al<sub>2</sub>O<sub>3</sub> and 3.867 wt%  $Y_2O_3$  using a universal testing machine at constant crosshead speeds, with initial strain rates between  $3 \times 10^{-4}$  and  $2 \times 10^{-5}$  s<sup>-1</sup> and at temperatures between 1873 and 2048 K in both argon and N<sub>2</sub> atmospheres.

In argon atmosphere, it was observed that:

1. Maximum tensile elongation reached 60% at an initial strain rate of  $5 \times 10^{-5}$  s<sup>-1</sup>, at 1998 K.

2. No phase transformation or multiplication of dislocation were observed in deformed samples.

3. The vaporization of grain-boundary phase and grain growth during tests prevented further elongation.

In  $N_2$  atmosphere, it was observed that:

4. A cry stalline phase was formed at the triple points and multi grain junctions during tension tests; consequently, the samples exhibited brittle fracture.

5. No phase transformation or multiplication of dislocation were observed in deformed samples.

6. The cracks were propagated in the vertical direction of tensile axis in deformed samples.

These results showed that the major deformation mechanism in the present study was grain-boundary sliding.

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